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AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Serial Number: 10/815,464 Filing Date: March 31, 2004

Title: METHOD OF EMBEDDING PASSIVE COMPONENT WITHIN VIA (as amended)

Assignee: Intel Corporation

IN THE CLAIMS

Please amend the claims as follows:

- 1. 31. (Canceled)
- 32. (Currently Amended) A method comprising:

forming a via in a substrate; and

forming an electrical component in the via in the substrate, wherein the electrical component includes at least a portion of memory.

- 33. (Previously Presented) The method of claim 32 wherein forming an electrical component in the via includes forming at least a portion of a resistor.
- 34. (Previously Presented) The method of claim 32 wherein forming an electrical component in the via includes forming at least a portion of a capacitor.
- 35. (Previously Presented) The method of claim 32 wherein forming an electrical component in the via includes forming at least a portion of a core.
- 36. (Previously Presented) The method of claim 32 wherein forming an electrical component in the via includes forming a resistor.
- 37. (Previously Presented) The method of claim 32 wherein forming an electrical component in the via includes forming a core.
- 38. (Canceled)
- 39. (Currently Amended) The method of claim 32 wherein forming an electrical component in the via includes forming a memory device.

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40. (Previously Presented) The method of claim 32 wherein the electrical component in the via

includes a passive electrical component.

41. (Previously Presented) The method of claim 32 wherein the electrical component in the via

is a passive electrical component.

42. (Currently Amended) The method of claim 32 wherein the electrical component [[is]]

includes a capacitor further comprising:

an inner cylindrical portion; and

an outer via portion substantially surrounding the inner cylindrical portion.

43. (Currently Amended) The method of claim 32 wherein the electrical component [[is]]

includes a capacitor further comprising:

a first curved portion; and

a second curved portion spaced from the first curved portion, wherein the distance

between the first curved portion and the second curved portion vary.

44. (Currently Amended) The method of claim 32 wherein the electrical component [[is]]

includes a capacitor further comprising:

a first curved portion; and

a second curved portion spaced from the first curved portion, wherein the first curved

portion and the second curved portion are portions of a via formed by insulating a first portion of

a via from a second portion of a via.

45. (Currently Amended) The method of claim 32 wherein forming an electrical component in

the via includes A method comprising:

forming a via in a substrate; and

forming at least a portion of a transformer within the via.

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46. - 68. (Canceled)

69. (New) A method comprising:

forming a via in a substrate; and

forming a capacitor in the via in the substrate, wherein forming the capacitor further comprises:

forming a first curved plate portion; and

forming a second curved plate portion spaced from the first curved plate portion, wherein the distance between the first curved plate portion and the second curved plate portion vary.

70. (New) A method comprising:

forming a via in a substrate; and

forming a capacitor in the via in the substrate, wherein forming the capacitor further comprises:

forming a first curved plate portion; and

forming a second curved plate portion spaced from the first curved plate portion, wherein the first curved plate portion and the second curved plate portion are portions of a via formed by insulating the first portion of a via from a second portion of a via.

(New) The method of claim 45 wherein forming at least a portion of a transformer within 71. the via includes forming a transformer within the via.

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